

Timothy D Sands

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

218
papers

10,101
citations

53
h-index

93
g-index

227
ext. papers

10,802
ext. citations

4.2
avg. IF

5.67
L-index

#	Paper	IF	Citations
218	Rocksalt nitride metal/semiconductor superlattices: A new class of artificially structured materials. <i>Applied Physics Reviews</i> , 2018 , 5, 021101	17.3	42
217	Temperature-dependent thermal and thermoelectric properties of n-type and p-type Sc _{1-x} Mg _x N. <i>Physical Review B</i> , 2018 , 97,	3.3	26
216	Tailoring of surface plasmon resonances in TiN/(Al _{0.72} Sc _{0.28})N multilayers by dielectric layer thickness variation. <i>Journal of Materials Science</i> , 2018 , 53, 4001-4009	4.3	15
215	Phonon wave effects in the thermal transport of epitaxial TiN/(Al,Sc)N metal/semiconductor superlattices. <i>Journal of Applied Physics</i> , 2017 , 121, 015109	2.5	31
214	Dislocation-pipe diffusion in nitride superlattices observed in direct atomic resolution. <i>Scientific Reports</i> , 2017 , 7, 46092	4.9	39
213	Compensation of native donor doping in ScN: Carrier concentration control and p-type ScN. <i>Applied Physics Letters</i> , 2017 , 110, 252104	3.4	42
212	Void-mediated coherency-strain relaxation and impediment of cubic-to-hexagonal transformation in epitaxial metastable metal/semiconductor TiN/Al _{0.72} Sc _{0.28} N multilayers. <i>Physical Review Materials</i> , 2017 , 1,	3.2	8
211	Cross-plane thermal conductivity of (Ti,W)N/(Al,Sc)N metal/semiconductor superlattices. <i>Physical Review B</i> , 2016 , 93,	3.3	55
210	Anisotropic Effects on the Thermoelectric Properties of Highly Oriented Electrodeposited Bi ₂ Te ₃ Films. <i>Scientific Reports</i> , 2016 , 6, 19129	4.9	65
209	Microstructural evolution and thermal stability of HfN/ScN, ZrN/ScN, and Hf _{0.5} Zr _{0.5} N/ScN metal/semiconductor superlattices. <i>Journal of Materials Science</i> , 2016 , 51, 8250-8258	4.3	18
208	Microstructural evolution and thermal stability of nitride-based metal/semiconductor superlattices for thermoelectric and hard-coating applications 2016 , 237-238		
207	Understanding the Rocksalt-to-Wurtzite phase transformation through microstructural analysis of (Al,Sc)N epitaxial thin films. <i>Applied Physics Letters</i> , 2016 , 109, 172102	3.4	10
206	Thermal stability of epitaxial cubic-TiN/(Al,Sc)N metal/semiconductor superlattices. <i>Journal of Materials Science</i> , 2015 , 50, 3200-3206	4.3	22
205	Effect of deposition pressure on the microstructure and thermoelectric properties of epitaxial ScN(001) thin films sputtered onto MgO(001) substrates. <i>Journal of Materials Research</i> , 2015 , 30, 626-634 ⁵	2.5	28
204	Development of epitaxial Al _x Sc _{1-x} N for artificially structured metal/semiconductor superlattice metamaterials. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 251-259	1.3	40
203	Epitaxial superlattices with titanium nitride as a plasmonic component for optical hyperbolic metamaterials. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2014 , 111, 7546-51	11.5	164
202	TiN/(Al,Sc)N metal/dielectric superlattices and multilayers as hyperbolic metamaterials in the visible spectral range. <i>Physical Review B</i> , 2014 , 90,	3.3	41

201	Bulk-Like Laminated Nitride Metal/Semiconductor Superlattices for Thermoelectric Devices. <i>Journal of Microelectromechanical Systems</i> , 2014 , 23, 672-680	2.5	9
200	Changing the academic culture: valuing patents and commercialization toward tenure and career advancement. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2014 , 111, 6542-7	11.5	53
199	Electrodeposition of InSb branched nanowires: Controlled growth with structurally tailored properties. <i>Journal of Applied Physics</i> , 2014 , 116, 083506	2.5	11
198	Enhanced hardness in epitaxial TiAlScN alloy thin films and rocksalt TiN/(Al,Sc)N superlattices. <i>Applied Physics Letters</i> , 2014 , 105, 151904	3.4	21
197	Electronic and optical properties of ScN and (Sc,Mn)N thin films deposited by reactive DC-magnetron sputtering. <i>Journal of Applied Physics</i> , 2013 , 114, 063519	2.5	38
196	Thermoelectric properties of epitaxial ScN films deposited by reactive magnetron sputtering onto MgO(001) substrates. <i>Journal of Applied Physics</i> , 2013 , 113, 153704	2.5	71
195	Titanium nitride as a plasmonic material for visible and near-infrared wavelengths [erratum]. <i>Optical Materials Express</i> , 2013 , 3, 1658	2.6	5
194	Cross-plane thermoelectric transport in p-type La _{0.67} Sr _{0.33} MnO ₃ /LaMnO ₃ oxide metal/semiconductor superlattices. <i>Journal of Applied Physics</i> , 2013 , 113, 193702	2.5	13
193	Effect of SrTiO ₃ thickness on the capacitance-voltage characteristics of (La,Sr)CoO ₃ /(Pb,Lu)(Zr,Ti)O ₃ /SrTiO ₃ /LaVO ₃ epitaxial heterostructures. <i>Applied Physics A: Materials Science and Processing</i> , 2012 , 109, 285-289	2.6	
192	Thermoelectric properties of HfN/ScN metal/semiconductor superlattices: a first-principles study. <i>Journal of Physics Condensed Matter</i> , 2012 , 24, 415303	1.8	18
191	Metal Nitrides for Plasmonic Applications 2012 ,		2
190	Titanium nitride as a plasmonic material for visible and near-infrared wavelengths. <i>Optical Materials Express</i> , 2012 , 2, 478	2.6	468
189	Cross-plane electronic and thermal transport properties of p-type La _{0.67} Sr _{0.33} MnO ₃ /LaMnO ₃ perovskite oxide metal/semiconductor superlattices. <i>Journal of Applied Physics</i> , 2012 , 112, 063714	2.5	10
188	Free standing GaN nano membrane by laser lift-off method. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1432, 53		4
187	Built-in electric field minimization in (In, Ga)N nanoheterostructures. <i>Nano Letters</i> , 2011 , 11, 4515-9	11.5	10
186	Magnetic manipulation and optical imaging of an active plasmonic single-particle Fe-Au nanorod. <i>Langmuir</i> , 2011 , 27, 15292-8	4	23
185	Controlled growth of ordered nanopore arrays in GaN. <i>Nano Letters</i> , 2011 , 11, 535-40	11.5	9
184	First-principles analysis of ZrN/ScN metal/semiconductor superlattices for thermoelectric energy conversion. <i>Journal of Applied Physics</i> , 2011 , 109, 083717	2.5	19

183	Room temperature device performance of electrodeposited InSb nanowire field effect transistors. <i>Applied Physics Letters</i> , 2011 , 98, 243504	3.4	29
182	Electronic structure, vibrational spectrum, and thermal properties of yttrium nitride: A first-principles study. <i>Journal of Applied Physics</i> , 2011 , 109, 073720	2.5	40
181	Capacitance-voltage modeling of metal-ferroelectric-semiconductor capacitors based on epitaxial oxide heterostructures. <i>Applied Physics Letters</i> , 2011 , 98, 102901	3.4	17
180	GaN nanostructure design for optimal dislocation filtering. <i>Journal of Applied Physics</i> , 2010 , 108, 074313	2.5	9
179	Novel metal/semiconductor nanocomposite and superlattice materials and devices for thermoelectrics 2010 ,		1
178	Dislocation filtering in GaN nanostructures. <i>Nano Letters</i> , 2010 , 10, 1568-73	11.5	100
177	III-nitride nanopyramid light emitting diodes grown by organometallic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2010 , 108, 044303	2.5	22
176	Electronic structure, phonons, and thermal properties of ScN, ZrN, and HfN: A first-principles study. <i>Journal of Applied Physics</i> , 2010 , 107, 033715	2.5	102
175	Electrodeposition of Indium Antimonide Nanowires in Porous Anodic Alumina Membranes 2010 ,		1
174	Capacitance-voltage characteristics of SrTiO ₃ /LaVO ₃ epitaxial heterostructures. <i>Applied Physics Letters</i> , 2010 , 96, 212903	3.4	7
173	Thermal conductivity of bismuth telluride nanowire array-epoxy composite. <i>Applied Physics Letters</i> , 2009 , 94, 223116	3.4	54
172	Self-supporting nanowire arrays templated in sacrificial branched porous anodic alumina for thermoelectric devices. <i>Applied Physics Letters</i> , 2009 , 95, 073108	3.4	15
171	. <i>IEEE Nanotechnology Magazine</i> , 2009 , 8, 469-476	2.6	10
170	Toward surround gates on vertical single-walled carbon nanotube devices. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 821		20
169	Linear Coefficient of Thermal Expansion of Porous Anodic Alumina Thin Films from Atomic Force Microscopy. <i>Nanoscale and Microscale Thermophysical Engineering</i> , 2009 , 13, 243-252	3.7	10
168	Thermomechanical and Thermal Contact Characteristics of Bismuth Telluride Films Electrodeposited on Carbon Nanotube Arrays. <i>Advanced Materials</i> , 2009 , 21, 4280-4283	24	13
167	Thermoelectric Transport in a ZrN/ScN Superlattice. <i>Journal of Electronic Materials</i> , 2009 , 38, 960-963	1.9	58
166	The use of polyethyleneimine to control the growth-front morphology of electrochemically deposited gold nanowires for engineered nanogap electrodes. <i>Small</i> , 2009 , 5, 2387-91	11	3

165	Pseudomorphic stabilization of rocksalt GaN in TiN/GaN multilayers and superlattices. <i>Physical Review B</i> , 2009 , 80,	3.3	11
164	Nanoscale design to enable the revolution in renewable energy. <i>Energy and Environmental Science</i> , 2009 , 2, 559	35.4	311
163	Thermal conductivity of (Zr,W)N/ScN metal/semiconductor multilayers and superlattices. <i>Journal of Applied Physics</i> , 2009 , 105, 024909	2.5	101
162	Organometallic vapor phase epitaxial growth of GaN on ZrN/InSb substrates. <i>Applied Physics Letters</i> , 2008 , 93, 023109	3.4	17
161	Highly ordered diamond and hybrid triangle-diamond patterns in porous anodic alumina thin films. <i>Applied Physics Letters</i> , 2008 , 93, 043108	3.4	30
160	Independently addressable fields of porous anodic alumina embedded in SiO ₂ on Si. <i>Applied Physics Letters</i> , 2008 , 92, 013122	3.4	17
159	Pulsed selective epitaxial growth of hexagonal GaN microprisms. <i>Journal of Crystal Growth</i> , 2008 , 310, 1107-1111	1.6	1
158	Controlled Decoration of Single-Walled Carbon Nanotubes with Pd Nanocubes. <i>Journal of Physical Chemistry C</i> , 2007 , 111, 13756-13762	3.8	20
157	Optimization of carbon nanotube synthesis from porous anodic Al ₂ O ₃ templates. <i>Carbon</i> , 2007 , 45, 2290-2296	10.4	14
156	Electrical properties of individual gold nanowires arrayed in a porous anodic alumina template. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 3152-3158	1.6	24
155	Nanopatterned Contacts to GaN. <i>Journal of Electronic Materials</i> , 2007 , 36, 359-367	1.9	6
154	In-place fabrication of nanowire electrode arrays for vertical nanoelectronics on Si substrates. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 343		20
153	Field emission from GaN and (Al,Ga)N/GaN nanorod heterostructures. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, L15		9
152	Dendrimer-assisted controlled growth of carbon nanotubes for enhanced thermal interface conductance. <i>Nanotechnology</i> , 2007 , 18, 385303	3.4	53
151	Effect of KOH treatment on the schottky barrier height and reverse leakage current in Pt/n-GaN. <i>Journal of Electronic Materials</i> , 2006 , 35, 107-112	1.9	9
150	High-reflectivity Al-Pt nanostructured Ohmic contact to p-GaN. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 2448-2453	2.9	9
149	Templated synthesis of gold-iron alloy nanoparticles using pulsed laser deposition. <i>Nanotechnology</i> , 2006 , 17, 5131-5135	3.4	12
148	Growth of TiN/GaN metal/semiconductor multilayers by reactive pulsed laser deposition. <i>Journal of Applied Physics</i> , 2006 , 100, 064901	2.5	22

147	GaN nanorod Schottky and p-n junction diodes. <i>Nano Letters</i> , 2006 , 6, 2893-8	11.5	74
146	A nanocapacitor with giant dielectric permittivity. <i>Nanotechnology</i> , 2006 , 17, 2284-2288	3.4	9
145	Dendrimer-assisted low-temperature growth of carbon nanotubes by plasma-enhanced chemical vapor deposition. <i>Chemical Communications</i> , 2006 , 2899-901	5.8	25
144	Vertical single- and double-walled carbon nanotubes grown from modified porous anodic alumina templates. <i>Nanotechnology</i> , 2006 , 17, 3925-3929	3.4	49
143	Dendrimer-templated Fe nanoparticles for the growth of single-wall carbon nanotubes by plasma-enhanced CVD. <i>Journal of Physical Chemistry B</i> , 2006 , 110, 10636-44	3.4	38
142	Lithography-free in situ Pd contacts to templated single-walled carbon nanotubes. <i>Nano Letters</i> , 2006 , 6, 2712-7	11.5	27
141	Faceted and vertically aligned GaN nanorod arrays fabricated without catalysts or lithography. <i>Nano Letters</i> , 2005 , 5, 1847-51	11.5	93
140	Equilibrium limits of coherency in strained nanowire heterostructures. <i>Journal of Applied Physics</i> , 2005 , 97, 114325	2.5	301
139	TiN/GaN Metal/Semiconductor Multilayer Nanocomposites Grown by Reactive Pulsed Laser Deposition. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 872, 1		2
138	Thermal properties of electrodeposited bismuth telluride nanowires embedded in amorphous alumina. <i>Applied Physics Letters</i> , 2004 , 85, 6001-6003	3.4	68
137	Effect of excimer laser annealing on the structural properties of silicon germanium films. <i>Journal of Materials Research</i> , 2004 , 19, 3503-3511	2.5	7
136	Heterogeneous integration of CdS filters with GaN LEDs for fluorescence detection microsystems. <i>Sensors and Actuators A: Physical</i> , 2004 , 111, 1-7	3.9	97
135	Calculating Seebeck Coefficients for Arbitrary Temperature Gradients. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 793, 383		
134	Excimer laser lift-off for packaging and integration of GaN-based light-emitting devices 2003 , 4977, 587		1
133	High-Density 40 nm Diameter Sb-Rich Bi ₂ Sb _x Te ₃ Nanowire Arrays. <i>Advanced Materials</i> , 2003 , 15, 1003-1006	11.5	130
132	Laser-driven formation of a high-pressure phase in amorphous silica. <i>Nature Materials</i> , 2003 , 2, 796-800	27	69
131	Microfabrication using one-step LPCVD porous polysilicon films. <i>Journal of Microelectromechanical Systems</i> , 2003 , 12, 418-424	2.5	17
130	Direct Electrodeposition of Highly Dense 50 nm Bi ₂ Te _{3-y} Se _y Nanowire Arrays. <i>Nano Letters</i> , 2003 , 3, 973-977	11.5	140

129	Electrodeposition of Bi _{1-x} Sb _x Films and 200-nm Wire Arrays from a Nonaqueous Solvent. <i>Chemistry of Materials</i> , 2003 , 15, 1676-1681	9.6	64
128	The electrodeposition of high-density, ordered arrays of Bi _{1-x} Sb _x nanowires. <i>Journal of the American Chemical Society</i> , 2003 , 125, 2388-9	16.4	118
127	Structure of Bismuth Telluride Nanowire Arrays Fabricated by Electrodeposition into Porous Anodic Alumina Templates. <i>Chemistry of Materials</i> , 2003 , 15, 335-339	9.6	160
126	A Coupled Cellular Automata Representation of Nanoscale Transport Across Semiconductor Interfaces. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 796, 85		1
125	Effect of oxygen partial pressure during pulsed laser deposition on the orientation of CeO ₂ thin films grown on (100) silicon. <i>Journal of Materials Research</i> , 2003 , 18, 1753-1756	2.5	2
124	Effects of KrF excimer laser irradiation on metal contacts to n-type and p-type GaN. <i>Journal of Applied Physics</i> , 2003 , 94, 3529-3535	2.5	24
123	Electrical properties of metal contacts on laser-irradiated n-type GaN. <i>Applied Physics Letters</i> , 2003 , 82, 580-582	3.4	19
122	Ferroelectric field effect in epitaxial LaVO ₃ /(Ba,Sr)/TiO ₃ /(Pb,La)(Zr,Ti)O ₃ /(La,Sr)CoO ₃ heterostructures. <i>Journal of Applied Physics</i> , 2003 , 93, 4761-4765	2.5	7
121	Modification of (Pb,La)(Zr,Ti)O ₃ thin films during pulsed laser liftoff from MgO substrates. <i>Journal of Applied Physics</i> , 2003 , 94, 4047-4052	2.5	17
120	Fabrication of High-Density, High Aspect Ratio, Large-Area Bismuth Telluride Nanowire Arrays by Electrodeposition into Porous Anodic Alumina Templates. <i>Advanced Materials</i> , 2002 , 14, 665-667	24	261
119	GaN microcavities formed by laser lift-off and plasma etching. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 93, 98-101	3.1	3
118	Insights into the Electrodeposition of Bi ₂ Te ₃ . <i>Journal of the Electrochemical Society</i> , 2002 , 149, C546	3.9	207
117	Pulsed Laser Annealing of Silicon-Germanium Films. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 741, 421		5
116	Processing and morphology of permeable polycrystalline silicon thin films. <i>Journal of Materials Research</i> , 2002 , 17, 2235-2242	2.5	8
115	Enhancement of (In,Ga)N light-emitting diode performance by laser liftoff and transfer from sapphire to silicon. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 1400-1402	2.2	22
114	Kinetics of the Pd/In thin-film bilayer reaction: Implications for transient-liquid-phase wafer bonding. <i>Journal of Electronic Materials</i> , 2001 , 30, 1471-1475	1.9	18
113	InGaN/GaN Quantum Well Microcavities Formed by Laser Lift-Off and Plasma Etching. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 228, 91-94	1.3	1
112	Comparative Study of the Crystallization Behavior of Fe-Cr-B-Si in Bulk and Thin Film Forms. <i>Journal of Materials Synthesis and Processing</i> , 2001 , 9, 181-185		3

111	Epitaxial growth of skutterudite (CoSb ₃) thin films on (001) InSb by pulsed laser deposition. <i>Journal of Materials Research</i> , 2001 , 16, 2467-2470	2.5	11
110	High-T _c superconducting NbN films with low particulate density grown at 25 °C using pulsed laser deposition. <i>Journal of Materials Research</i> , 2001 , 16, 1223-1226	2.5	14
109	Energy deposition at front and rear surfaces during picosecond laser interaction with fused silica. <i>Applied Physics Letters</i> , 2001 , 78, 2840-2842	3.4	32
108	Optical spectroscopy of GaN microcavities with thicknesses controlled using a plasma etchback. <i>Applied Physics Letters</i> , 2001 , 79, 3029-3031	3.4	27
107	Pulsed laser deposition of skutterudite thin films. <i>Journal of Applied Physics</i> , 2001 , 89, 3508-3513	2.5	36
106	Electrodeposition of ordered Bi ₂ Te ₃ nanowire arrays. <i>Journal of the American Chemical Society</i> , 2001 , 123, 7160-1	16.4	271
105	The Materials Science of Permeable Polysilicon Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 687, 1		
104	Discrete State Simulation of Electrical Conductivity and the Peltier Effect for Arbitrary Band Structures. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 691, 1		2
103	Evaluation of (In,Ga)N Films as Optical Absorption Filters for Application in Integrated Fluorescence Detection Micro-Bioanalytical Systems. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 693, 1		
102	Electrodeposition of Bi ₂ Te ₃ Nanowire Composites. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 626, 1411		1
101	Preparation and Optical Characterization of Sol-Gel Deposited Pb(Zr _{0.45} Ti _{0.55})O ₃ Films. <i>Journal of Sol-Gel Science and Technology</i> , 2000 , 19, 157-162	2.3	9
100	Machining of transparent materials using an IR and UV nanosecond pulsed laser. <i>Applied Physics A: Materials Science and Processing</i> , 2000 , 71, 601-608	2.6	38
99	Thermal conductivity of skutterudite thin films and superlattices. <i>Applied Physics Letters</i> , 2000 , 77, 3854-3856	3.4	42
98	Bimodal spatial distribution of pores in anodically oxidized aluminum thin films. <i>Journal of Applied Physics</i> , 2000 , 88, 6875-6880	2.5	12
97	In _x Ga _{1-x} N light emitting diodes on Si substrates fabricated by Pd thin metal bonding and laser lift-off. <i>Applied Physics Letters</i> , 2000 , 77, 2822-2824	3.4	159
96	Epitaxial ferroelectric (Pb, La)(Zr, Ti)O ₃ thin films on stainless steel by excimer laser liftoff. <i>Applied Physics Letters</i> , 2000 , 76, 227-229	3.4	44
95	Epitaxial growth of semiconducting LaVO ₃ thin films. <i>Journal of Materials Research</i> , 2000 , 15, 1-3	2.5	18
94	Structural and chemical characterization of free-standing GaN films separated from sapphire substrates by laser lift-off. <i>Applied Physics Letters</i> , 2000 , 77, 1819	3.4	47

93	Magneto-optical properties of chromium-alloyed manganese bismuth thin films. <i>Journal of Applied Physics</i> , 1999 , 86, 1596-1603	2.5	7
92	Fluence effects on the magnetic properties of Fe ₈₁ B _{13.5} Si _{3.5} C ₂ metallic glass produced by pulsed laser deposition. <i>Journal of Applied Physics</i> , 1999 , 85, 6652-6654	2.5	16
91	Reduction of the energy gap pressure coefficient of GaN due to the constraining presence of the sapphire substrate. <i>Journal of Applied Physics</i> , 1999 , 85, 2385-2389	2.5	78
90	Integration of GaN thin films with dissimilar substrate materials by Pd-In metal bonding and laser lift-off. <i>Journal of Electronic Materials</i> , 1999 , 28, 1409-1413	1.9	43
89	Structural and optical quality of GaN/metal/Si heterostructures fabricated by excimer laser lift-off. <i>Applied Physics Letters</i> , 1999 , 75, 1887-1889	3.4	52
88	Fabrication of thin-film InGaN light-emitting diode membranes by laser lift-off. <i>Applied Physics Letters</i> , 1999 , 75, 1360-1362	3.4	284
87	The influence of the sapphire substrate on the temperature dependence of the GaN bandgap. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 572, 289		0
86	Damage-free separation of GaN thin films from sapphire substrates. <i>Applied Physics Letters</i> , 1998 , 72, 599-601	3.4	322
85	Simple Ru electrode scheme for ferroelectric (Pb,La)(Zr,Ti)O ₃ capacitors directly on silicon. <i>Journal of Applied Physics</i> , 1998 , 84, 1121-1125	2.5	22
84	Decoupling the structural and magnetic phase transformations in magneto-optic MnBi thin films by the partial substitution of Cr for Mn. <i>Applied Physics Letters</i> , 1998 , 72, 2337-2339	3.4	22
83	Quantitative damage morphology analysis of laser-induced surface cracks in fused silica at 355 nm. 1998 , 3244, 348		2
82	Comparison of the critical current anisotropy in epitaxial YBa ₂ Cu ₃ O _{7-x} films on (100) LaAlO ₃ and (100) yttria stabilized zirconia. <i>Journal of Materials Research</i> , 1994 , 9, 270-274	2.5	2
81	Electro-optic potassium-tantalate-niobate films prepared by pulsed laser deposition from segmented pellets. <i>Journal of Materials Research</i> , 1994 , 9, 1272-1279	2.5	8
80	Oriented ferroelectric La-Sr-Co-O/Pb-La-Zr-Ti-O/La-Sr-Co-O heterostructures on [001] Pt/SiO ₂ Si substrates using a bismuth titanate template layer. <i>Applied Physics Letters</i> , 1994 , 64, 2511-2513	3.4	134
79	Scaling of ferroelectric properties in La-Sr-Co-O/Pb-La-Zr-Ti-O/La-Sr-Co-O capacitors. <i>Applied Physics Letters</i> , 1994 , 64, 1588-1590	3.4	45
78	Magnetic properties of epitaxial MnAl/NiAl magnetic multilayers grown on GaAs heterostructures (invited). <i>Journal of Applied Physics</i> , 1994 , 75, 6665-6669	2.5	2
77	Epitaxial ferroelectric thin films for memory applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1994 , 22, 283-289	3.1	50
76	Magnetotransport properties of MBE-grown magnetic superlattices of Mn-based intermetallics on GaAs heterostructures. <i>Solid-State Electronics</i> , 1994 , 37, 1031-1036	1.7	7

75	Template approaches to growth of oriented oxide heterostructures on SiO ₂ /Si. <i>Journal of Electronic Materials</i> , 1994 , 23, 19-23	1.9	31
74	Epitaxial growth of ferromagnetic ultrathin MnGa films with perpendicular magnetization on GaAs. <i>Applied Physics Letters</i> , 1993 , 62, 1565-1567	3.4	185
73	Non-volatile memory characteristics of submicrometre Hall structures fabricated in epitaxial ferromagnetic MnAl films on GaAs. <i>Electronics Letters</i> , 1993 , 29, 421	1.1	16
72	Epitaxial MnAl/NiAl magnetic multilayers on AlAs/GaAs. <i>Applied Physics Letters</i> , 1993 , 63, 839-841	3.4	12
71	Epitaxial [(Mn,Ni)Al]/(Al,Ga)As heterostructures: Magnetic and magneto-optic properties. <i>Journal of Applied Physics</i> , 1993 , 73, 6121-6123	2.5	9
70	Microstructure of epitaxial La _{0.5} Sr _{0.5} CoO ₃ /ferroelectric Pb _{0.9} La _{0.1} (Zr _{0.2} Ti _{0.8}) _{0.975} O ₃ /La _{0.5} Sr _{0.5} CoO ₃ heterostructures on LaAlO ₃ . <i>Applied Physics Letters</i> , 1993 , 63, 1628-1630	3.4	53
69	Epitaxial MnGa/NiGa magnetic multilayers on GaAs. <i>Applied Physics Letters</i> , 1993 , 63, 696-698	3.4	40
68	Effect of crystallographic orientation on ferroelectric properties of PbZr _{0.2} Ti _{0.8} O ₃ thin films. <i>Applied Physics Letters</i> , 1993 , 63, 731-733	3.4	83
67	The extraordinary Hall effect in coherent epitaxial [(Mn,Ni)Al] thin films on GaAs. <i>Journal of Applied Physics</i> , 1993 , 73, 6399-6401	2.5	6
66	Electro-optic properties of single crystalline ferroelectric thin films. <i>Applied Physics Letters</i> , 1993 , 63, 596-598	3.4	46
65	MBE growth of ferromagnetic (Mn,Ni)Al thin films on AlAs/GaAs. <i>Journal of Crystal Growth</i> , 1993 , 127, 650-654	1.6	9
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